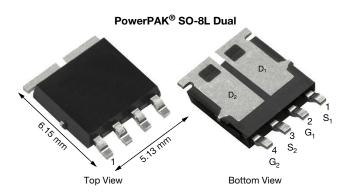
Vishay Siliconix

# Automotive Dual N-Channel 75 V (D-S) 175 °C MOSFET



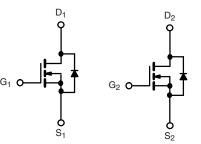
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	75			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.050			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.066			
I <sub>D</sub> (A) per leg	8			
Configuration	Dual			

#### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>q</sub> and UIS Tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



HALOGEN FREE



N-Channel MOSFET N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ980AEP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS	<b>S</b> (T <sub>C</sub> = 25 °C, unles	ss otherwise noted	)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	75	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	1	17		
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	10		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	30	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	68		
Single Pulse Avalanche Current  L = 0.1 mH		I <sub>AS</sub>	14		
Single Pulse Avalanche Energy	L = U.1 IIIII	E <sub>AS</sub>	10	mJ	
Mayimum Dayyar Dissinationh	T <sub>C</sub> = 25 °C	р	34	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	11		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) <sup>e, f</sup>		-	260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	85	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	4.3	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection..
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	•					
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	75	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 75 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 75 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 75 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-		Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 3.8 A	=.	0.041	0.050	
Drain Cauras On State Besistance	В	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 3.8 A, T <sub>J</sub> = 125 °C	=.	-	0.089	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 3.8 A, T <sub>J</sub> = 175 °C	-	-	0.116	Ω
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 3.3 A	-	0.055	0.066	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 3.8 A		-	14	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			=.	630	790	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 35 \text{ V}, f = 1 \text{ MHz}$	=.	84	105	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	]		=.	36	45	
Total Gate Charge <sup>c</sup>	Qg			-	14	21	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 35 \text{ V}, I_{D} = 9.7 \text{ A}$	=.	2.3	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	]		=.	2.9		
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1.3	2.67	4	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	14	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 35 \text{ V}, R_L = 35 \Omega$ - 10 $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ - 16		10	15	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			16	24		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	18	1
Source-Drain Diode Ratings and Char-	acteristics <sup>b</sup>						<u> </u>
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	68	Α
Forward Voltage	$V_{SD}$	le :	= 2.4 A, V <sub>GS</sub> = 0	-	0.8	1.1	V

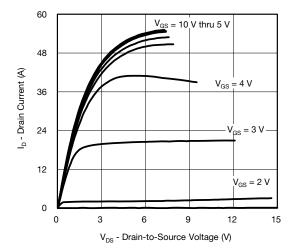
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

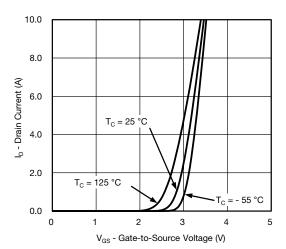
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



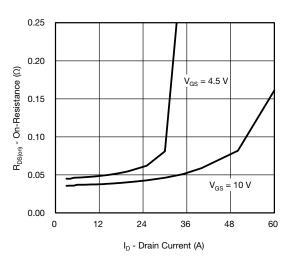
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



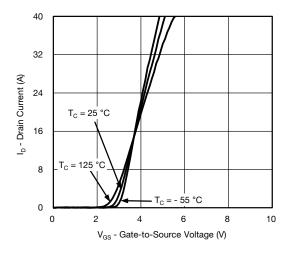
#### **Output Characteristics**



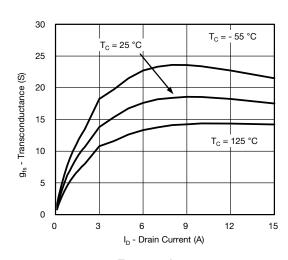
#### **Transfer Characteristics**



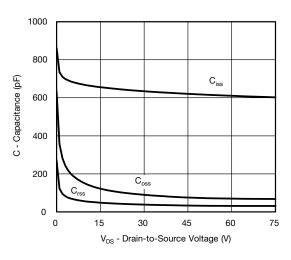
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



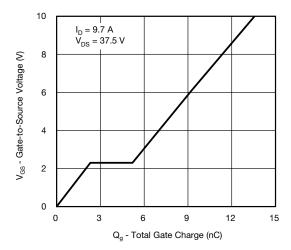
### Transconductance



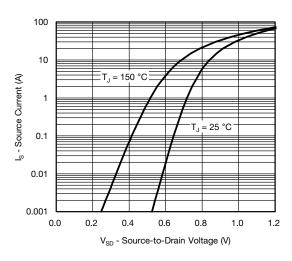
Capacitance



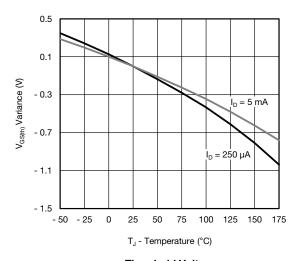
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



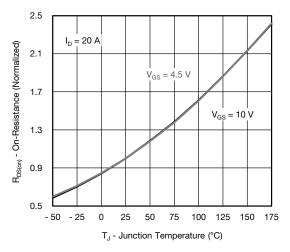
#### **Gate Charge**



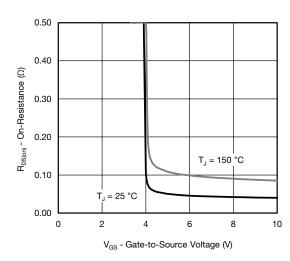
Source Drain Diode Forward Voltage



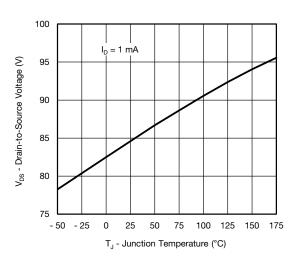
Threshold Voltage



On-Resistance vs. Junction Temperature



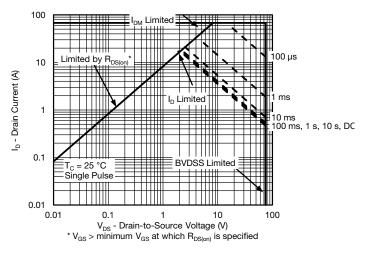
On-Resistance vs. Gate-to-Source Voltage



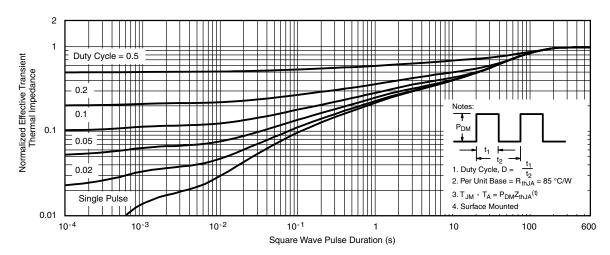
**Drain Source Breakdown vs. Junction Temperature** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



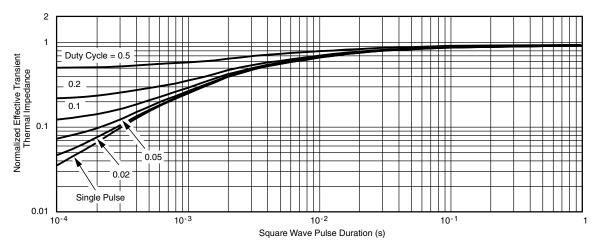
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62833">www.vishay.com/ppg?62833</a>.



# PowerPAK® SO-8L Case Outline 2



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DIM.	MILLIMETERS			INCHES				
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094		0.004				
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
Е	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23		0.009				
W1	0.41		0.016					
W2	2.82		0.111					
W3		2.96			2.96 0.117			
θ	0°	-	10°	0°	-	10°		

ECN: C21-1498-Rev. C, 01-Nov-2021

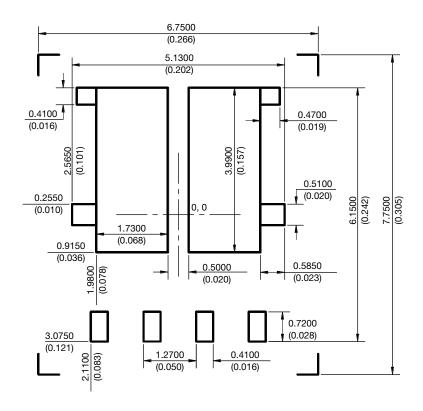
DWG: 6044

### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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